



30V N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8 (SWP) (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
	11mΩ @ V _{GS} = 10V	50A
30V	13mΩ @ V _{GS} = 4.5V	45A

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- Power Management Functions
- DC-DC Converters

Features and Benefits

- Low R_{DS(ON)} Ensures On State Losses Are Minimized
- 100% Unclamped Inductive Switching (Test in Production) Ensures More Reliable
- Small Form Factor Thermally Efficient Package Enables Higher Density End Products
- Occupies Just 33% of The Board Area Occupied by SO-8 Enabling Smaller End Product
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- PPAP Capable (Note 4)

Mechanical Data

- Case: PowerDI[®]3333-8 (SWP) (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound.
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.03 grams (Approximate)

PowerDI3333-8 (SWP) (Type UX)



G S S Pin1

Bottom View

G S
Equivalent Circuit

Top View

Ordering Information (Note 5)

 Part Number
 Case
 Packaging

 DMT3009LFVWQ-7
 PowerDI3333-8 (SWP) (Type UX)
 2,000/Tape & Reel

 DMT3009LFVWQ-13
 PowerDI3333-8 (SWP) (Type UX)
 3,000/Tape & Reel

Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to https://www.diodes.com/quality/.
- 5. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



SH9= Product Type Marking Code

YYWW = Date Code Marking

YY = Last Two Digits of Year (ex: 18 = 2018)

WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	30	V	
Gate-Source Voltage	V_{GSS}	±20	V	
	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	ΔD	12 10	А
Continuous Drain Current V _{GS} = 10V	$T_C = +25$ °C $T_C = +70$ °C	Ι _D	50 37	А
Maximum Continuous Body Diode Forward Current (Note 6)	Is	3	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I _{DM}	90	Α	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	90	Α	
Avalanche Current, L = 0.1mH	I _{AS}	19	Α	
Avalanche Energy, L = 0.1mH	Eas	19	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

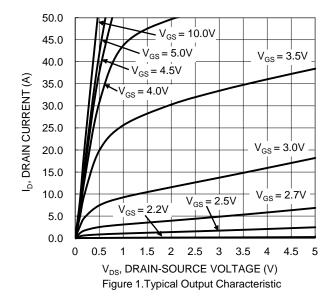
Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 6)	$T_A = +25^{\circ}C$	P_{D}	2.3	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	55	°C/W
Total Power Dissipation (Note 9)	$T_C = +25$ °C	P_{D}	35.7	W
Thermal Resistance, Junction to Case (Note 9) Steady State		$R_{ heta JC}$	3.5	°C/W
Operating and Storage Temperature Range	T _{J,} T _{STG}	-55 to +150	°C	

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	30	-	-	٧	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	-	-	1	μΑ	$V_{DS} = 24V$, $V_{GS} = 0V$	
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(TH)}	1	-	3	٧	$V_{DS} = V_{GS}$, $I_D = 250\mu A$	
	R _{DS(ON)}	1	6.6	11	mΩ	$V_{GS} = 10V, I_D = 14.4A$	
Static Drain-Source On-Resistance		-	10.5	13		$V_{GS} = 4.5V, I_{D} = 7A$	
		-	13.4	20		$V_{GS} = 3.8V, I_D = 5A$	
Diode Forward Voltage	V _{SD}	-	0.8	1.2	V	$V_{GS} = 0V, I_{S} = 10A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	823	-	pF	151/11/ 01/	
Output Capacitance	Coss	-	352	-	pF	$V_{DS} = 15V, V_{GS} = 0V,$ -f = 1.0MHz	
Reverse Transfer Capacitance	C _{rss}	-	52	-	pF	11 = 1.0WHZ	
Gate Resistance	Rg	-	1.2	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Q_{g}	-	5.8	-	nC		
Total Gate Charge (V _{GS} = 10V)	Qq	-	12	-	nC	151/ 1 44.44	
Gate-Source Charge	Qgs	-	1.7	-	nC	V _{DS} = 15V, I _D = 14.4A	
Gate-Drain Charge	Q _{qd}	-	2.4	-	nC		
Turn-On Delay Time	t _{D(ON)}	-	3.2	-	ns		
Turn-On Rise Time	t _R	-	5.2	-	ns	$V_{GS} = 10V, V_{DD} = 15V,$ $R_G = 1\Omega, I_D = 10A$	
Turn-Off Delay Time	t _{D(OFF)}	-	8.9	-	ns		
Turn-Off Fall Time	t _F	-	1.5	-	ns		
Body Diode Reverse Recovery Time	t _{RR}	-	16.4	-	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	-	5.9	-	nC	I _F = 10A, dI/dt = 100A/μs	

6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. Short duration pulse test used to minimize self-heating effect.
8. Guaranteed by design. Not subject to product testing.
9. Thermal resistance from junction to soldering point (on the exposed drain pad). Notes:





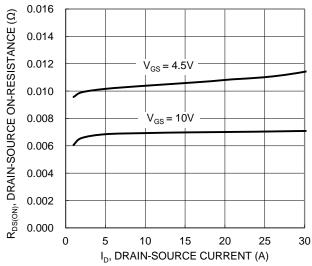


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

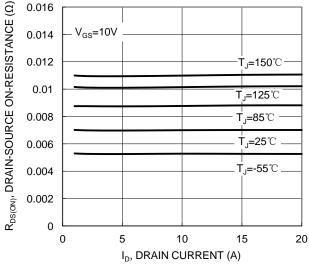
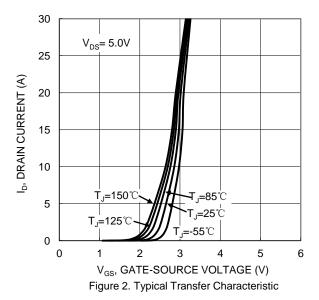
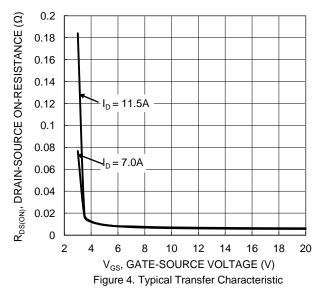


Figure 5. Typical On-Resistance vs. Drain Current and Temperature





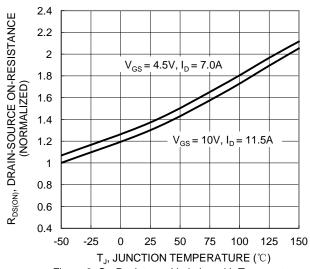


Figure 6. On-Resistance Variation with Temperature



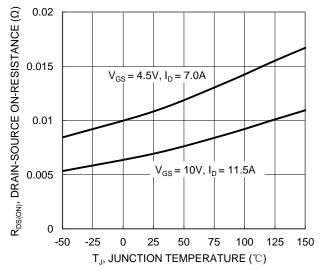


Figure 7. On-Resistance Variation with Temperature

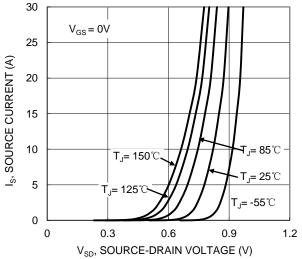
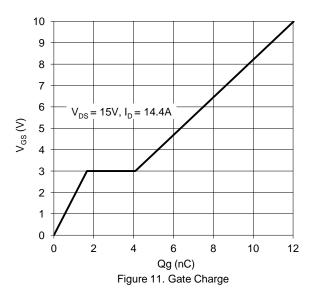


Figure 9. Diode Forward Voltage vs. Current



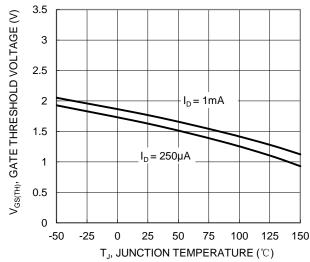
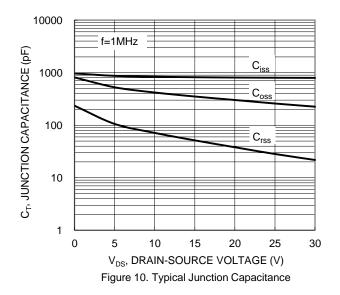
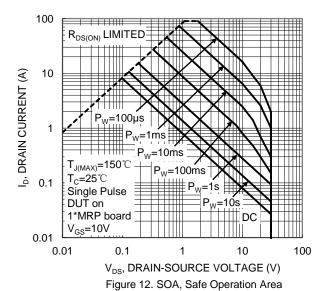


Figure 8. Gate Threshold Variation vs Junction Temperature







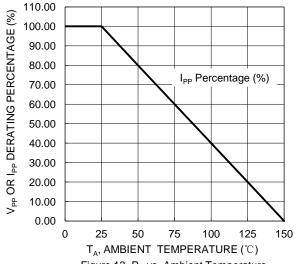


Figure 13. P_D vs. Ambient Temperature

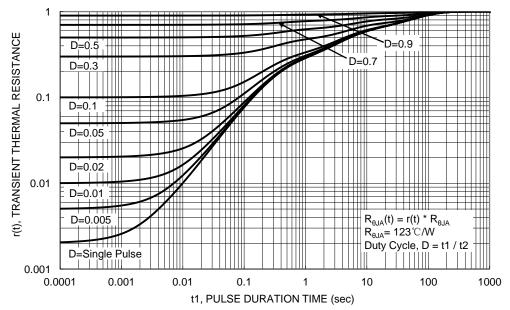


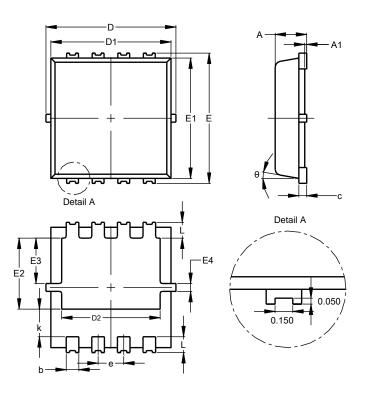
Figure 14. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)

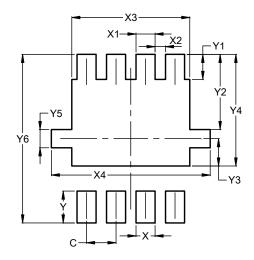


PowerDI3333-8 (SWP)						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
С	0.10	0.25	0.15			
D	3.20	3.40	3.30			
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E3	0.95	1.35	1.15			
E4	0.10	0.30	0.20			
е	_	_	0.65			
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All Dimensions in mm						

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.600
X4	3.500
Υ	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700



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